

# 3C-SiC / Si GaN 用异质外延晶体基板

## 3C-SiC/Si Heteroepitaxial substrates for GaN

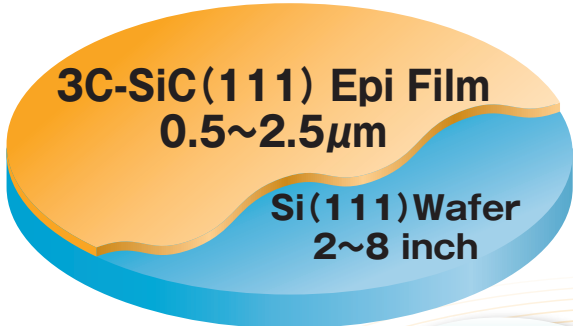
Air Water 的 3C-SiC / Si 异质外延晶圆是适合 GaN 生长的基板,其中 SiC 使用独特的外延膜形成技术在硅晶圆上异质外延生长。可以实现适用于 GaN 功率器元件和 GaN 高频器元件(无裂纹,无回熔,GaN 厚膜等)的 GaN 层之质量,并可提供使用于硅晶圆的大直径基板。

AWI 3C-SiC(111)/Si heteroepitaxial wafers using AW-original epitaxial technologies are one of the most suitable substrates for GaN devices. The 3C-SiC heteroepitaxial technology can realize large diameter substrates, on which high quality GaN layers can be easily grown using simple buffers.

► Air Water 的 3C-SiC/Si GaN 用异质外延晶体截面示意图  
 | A schematic cross section of AWI 3C-SiC/Si heteroepitaxial wafers for GaN

► 3C-SiC/Si 异质外延晶圆规格  
 | Specification of 3C-SiC/Si wafers

|              |                                                                                          |
|--------------|------------------------------------------------------------------------------------------|
| Diameter     | 2"~8" diameter                                                                           |
| Epi film     | 0.5~2.5 um-thick SiC(111) layer                                                          |
| Crystal      | XRC-FWHM (SiC(111), $\omega$ -scan) <1,600 arcsec @ 1 $\mu$ m, <900 arcsec @ 2.5 $\mu$ m |
| Applications | GaN-power, GaN-RF and so on.                                                             |



- 通过在Si基板上使用SiC, 与普通的GaN相比,具有右方显示之优势
- 不会发生熔蚀  
→可减低Chamber清洁的频繁  
→有助于提高良率
  - 可提高GaN的结晶性
  - 可改善散热性(横向)
  - 可容易减少裂纹

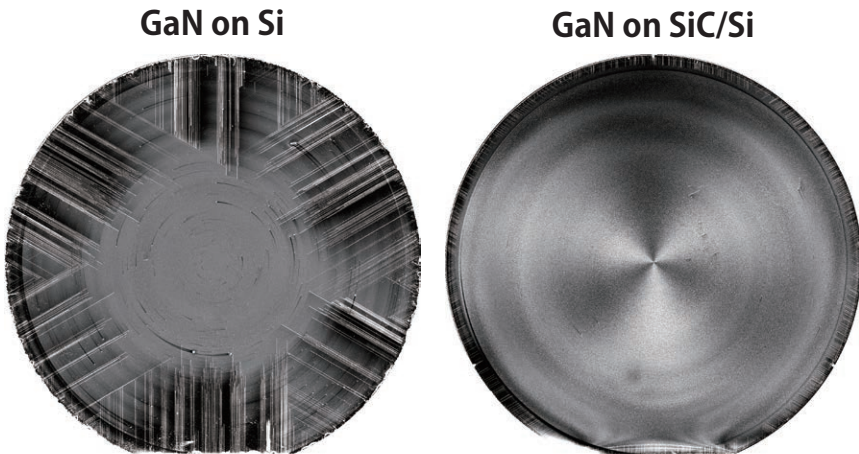
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## 3C-SiC/Si Heteroepitaxial substrates for GaN

### 在 6 英寸 3C-SiC / Si 基板的 Air Water 独有 GaN HEMT 构造范例 An example of AW original GaN HEMT on 6" 3C-SiC/Si substrates

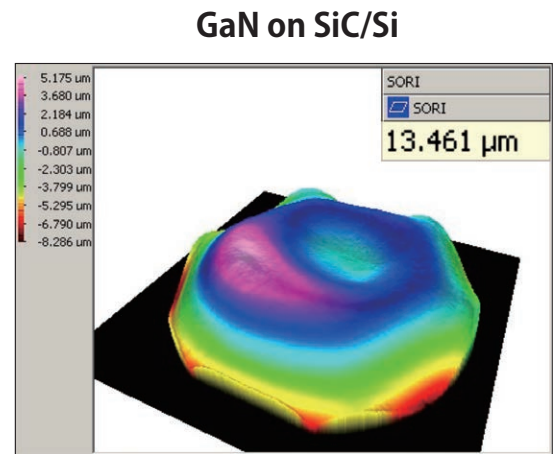
▶ 通过厚的 GaN 膜形成 6" GaN on Si 和 6" GaN on SiC/Si  
Comparison of 6" thick GaN on Si and 6" thick GaN on SiC/Si

激光散射图像 (氮化膜厚度 8 μm)  
可以形成没有裂纹的厚膜 GaN

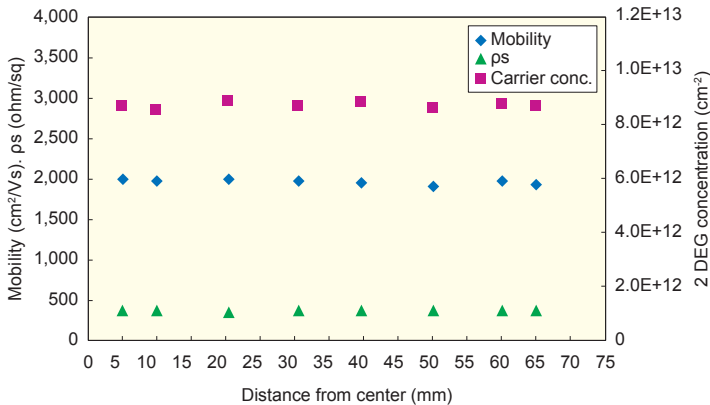


▶ 厚膜 6" GaN on SiC/Si 基板的弯曲  
SORI control of 6" thick GaN on SiC/Si

SORI 评估 (氮化膜厚度 8 μm)  
在 GaN 膜形成过程中可以控制翘曲



▶ AW 独有 6" GaN on SiC/Si  
电子迁移率, 薄层电阻, 载流子浓度评估  
Electron mobility, Sheet resistance, Carrier conc. of AW original GaN HEMT on 6" 3C-SiC/Si substrates



▶ AW 独有 6" GaN on SiC/Si  
电流 - 电压特性 (垂直流失电流 / 电压评估)  
Vertical I-V characteristic of AW original GaN HEMT on 6" 3C-SiC/Si substrates

